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**INITIAL PRODUCT/PROCESS CHANGE NOTIFICATION**  
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**13 May 2009**

**SUBJECT: ON Semiconductor Initial Product/Process Change Notification #16249**

**TITLE: Trench Die Transfer to Aizu and Gresham Wafer Fab Facilities**

**PROPOSED FIRST SHIP DATE: From Wafer Fab in Aizu, Japan , 10-Sept-2009**  
**From Wafer Fab in Gresham, Oregon, USA, 10-Jan-2010**

**AFFECTED CHANGE CATEGORY: ON Semi FAB Site**

**AFFECTED PRODUCT DIVISION: PowerFET Business Unit**

**FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:**

Contact Sales Office or Jennie Shen <[Jennie.Shen@onsemi.com](mailto:Jennie.Shen@onsemi.com)>

**NOTIFICATION TYPE:**

Initial Product/Process Change Notification (IPCN)

First change notification sent to customers. IPCNs are issued at least 120 days prior to implementation of the change. An IPCN is advance notification about an upcoming change and contains general information regarding the change details and devices affected. It also contains the preliminary reliability qualification plan.

The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN).

This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 90 days prior to implementation of the change.

**DESCRIPTION AND PURPOSE:**

This is an Initial Process Change Notification.

For the listed products, this is an announcement that the ON Semiconductor's Wafer Fab facilities in Aizu, Japan, and Gresham, Oregon, along with the current Wafer Foundry will all be sources for this Trench MOSFET Die.

The Aizu Fab facility is fully certified, and has been a continuous source for MOSFET Die for over 20-years. This particular Trench MOSFET platform has been qualified in the Aizu Wafer Fab facility since May 2007. The Gresham Fab facility is also fully certified, and has been a source for MOSFET Die since January 2007.

Device quality and reliability will continue to meet our high standards.



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**QUALIFICATION PLAN:**

Test: High Temperature Reverse Bias (HTRB)  
Conditions:  $V_{ds} = 80\% V_{ds \text{ rating}}$ ,  $T_a = 150^\circ\text{C}$ , 504-Hrs

Test: High Temperature Gate Bias (HTGB)  
Conditions:  $V_{gs} = 100\% V_{gs}$ ,  $T_a = 150^\circ\text{C}$ , 504-Hrs.

Test: Intermittent Operating Life (IOL-PC)  
Conditions:  $T_a = +25^\circ\text{C}$ ,  $\Delta T_j = 100^\circ\text{C}$ , 2-min on/off, 7.5K-cycles

Test: Temperature Cycling (TC-PC)  
Conditions:  $T_a = -65^\circ\text{C}/+150^\circ\text{C}$ , Air-to-Air, Dwell  $\geq 10$ -min, 500-cy

Test: Highly Accelerated Stress Test (HAST-PC)  
Conditions:  $T_a = 130^\circ\text{C}$ , RH=85%, P=18.8psig, 96-Hrs

Test: Highly Accelerated Stress Test (HAST-PC)  
Conditions:  $T_a = 121^\circ\text{C}$ , RH=100%, P=15psig, 96-Hrs



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**AFFECTED DEVICE LIST:**

2N7002ET1G  
2N7002ET3G  
2N7002KT1G  
2N7002KT1H  
2N7002KT3G  
2N7002WT1G  
2N7002WT3G  
NCP3101BMNTXG  
NCP347MTAETBG  
NCP347MTAFTBG  
NCP347MTAHTBG  
NCP347MTAITBG  
NCP348AEMTTBG  
NCP348AEMTTXG  
NCP348AEMUTBG  
NCP348AEMUTXG  
NCP348MTTBG  
NCP348MTTXG  
NTD95N02RT4G  
NTGD3133PT1G  
NTGD3133PT1H  
NTGD3147FT1G  
NTGD3148NT1G  
NTGD3149CT1G  
NTGD4161PT1G  
NTGD4167CT1G  
NTGD4169FT1G  
NTGS1135PT1G  
NTGS3130NT1G  
NTGS3441BT1G  
NTGS3447PT1G  
NTGS4111PT1  
NTGS4111PT1G  
NTGS4111PT2G  
NTGS4141NT1  
NTHD2110TT1G  
NTJD5121NT1G  
NTJD5121NT2G  
NTJS3151PT1  
NTJS3151PT1G  
NTJS3151PT2  
NTJS3151PT2G  
NTLJD2104PTAG  
NTLJD2104PTBG  
NTLJD2105LTBG  
NTLJD3115PT1G  
NTLJD3115PTAG  
NTLJD3119CTAG  
NTLJD3119CTBG  
NTLJD4116NT1G  
NTLJD4150PTBG  
NTLJF3117PT1G  
NTLJF3117PTAG



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NTLJF3118NTAG  
NTLJF3118NTBG  
NTLJF4156NT1G  
NTLJF4156NTAG  
NTLJS1102PTAG  
NTLJS1102PTBG  
NTLJS2103PTAG  
NTLJS2103PTBG  
NTLJS3113PT1G  
NTLJS3113PTAG  
NTLJS4114NT1G  
NTLJS4149PTAG  
NTLJS4149PTBG  
NTLJS4159NT1G  
NTVD3144NT2G  
NTVS3141PT2G  
NTZD5110NT1G  
NTZD5110NT5G  
NUS3045MNT1  
NUS3045MNT1G  
NUS3046MNT1G  
NUS3055MUTAG  
NUS3065MUTAG  
NUS3116MTR2G  
NUS5531MTR2G  
NUS6189MNTWG  
STLJD3115PT1G  
STLJD3115PTAG